



A Product Line of **Diodes Incorporated**



ZHB6718

20V BIPOLAR TRANSISTOR H-BRIDGE

Features

- Compact design •
- Operates up to 20V supply •
- 2.5A continuous rating
- NPN Transistor
 - $BV_{CEO} > 20$
- . Low Saturation Voltage V_{CE(sat)} < 150mV @ 1A **PNP** Transistor

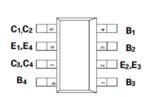
 - $BV_{CEO} > -20V$.
- Low Saturation Voltage V_{CE(sat)} < -200mV @ -1A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SM-8 (8 LEAD SOT223)
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.117 grams (approximate)

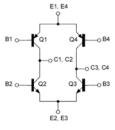


Top View



Top View

Pinout



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZHB6718TA	ZHB6718	7	12	1,000
ZHB6718TC	ZHB6718	13	12	4,000

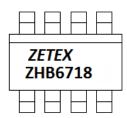
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information







Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	NPN	PNP	Unit
Collector-Base Voltage	V _{CBO}	20	-20	V
Collector-Emitter Voltage	V _{CEO}	20	-20	V
Emitter-Base Voltage	V _{EBO}	7	-7	V
Continuous Collector Current	Ic	2.5	-2.5	A
Peak Pulse Current (Note 5)	I _{CM}	6	-6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Collector Power Dissipation	(Note 5)	Р	1.25		
Collector Power Dissipation	(Note 6)	PD	2		
Thermal Desistance Junction to Ambient	(Note 5)	D	100	0000	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	62.5	°C/W	
Operating and Storage Temperature Range		T _J ,T _{STG}	-55 to +150	°C	

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

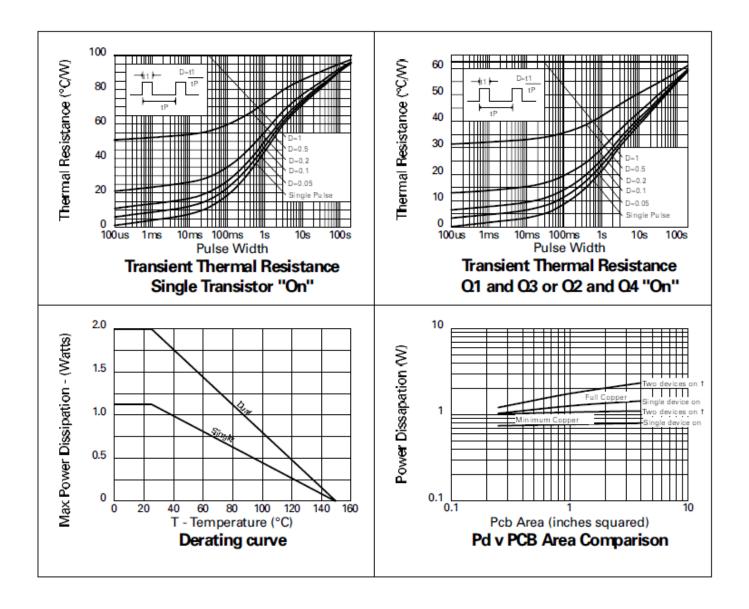
5. For a device with any single die active and mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
6. Same as note (5), except both Q1/Q3 active or Q2/Q4 active and equally sharing power. Notes:

7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



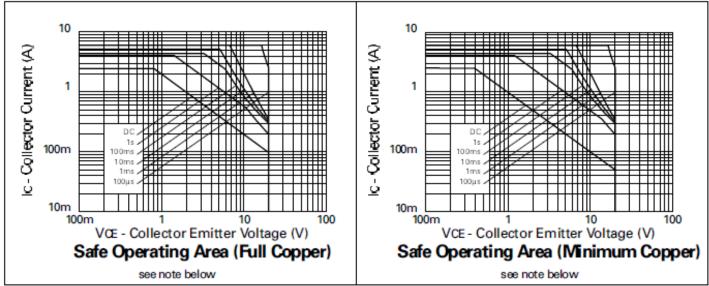


Thermal Characteristics and Derating Information









Note: The Safe Operating Area (SOA) charts shown are a combination of the worst case secondary breakdown characteristics for the NPN/PNP pair, and the thermal curves demonstrating the power dissipation capability of the energised ZHB part (opposing NPN-PNP switched on) when mounted on a 50mm x 50mm FR4 PCB. The two cases show:

i) full copper present and

ii) with minimal copper present - this being defined as an SM-8 footprint with 1.5mm tracks to the edge of the PCB.

For example, on a 50mm x 50mm full copper PCB, the ZHB6718 will safely dissipate 2W under DC conditions, taking note of continuous current ratings and voltage limits. Higher powers can be tolerated for pulsed operation, while the shorter pulse widths (100 µs and 1ms) being relevant for assessment of switching conditions.





Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	20	100	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	20	27	_	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	8.3	_	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	-	_	0.1	μA	V _{CB} = 16V
Emitter Cutoff Current	I _{EBO}	_	—	0.1	μA	V _{EB} = 4V
	hfe	200	400	—		$I_{C} = 10 \text{mA}, V_{CE} = 2 \text{V}$
DC autrent transfer Ctatic ratio (Nate 0)		300	450	300		$I_{C} = 100 \text{mA}, V_{CE} = 2 \text{V}$
DC current transfer Static ratio (Note 8)		200	360	_		$I_{C} = 2A, V_{CE} = 2V$
			180	_		$I_{C} = 6A, V_{CE} = 2V$
	V _{CE(sat)}	_	8	15	mV	$I_{C} = 0.1A, I_{B} = 10mA$
Collector-Emitter Saturation Voltage (Note 8)		_	70	150		$I_{\rm C} = 1$ A, $I_{\rm B} = 10$ mA
		_	130	200		$I_{C} = 2.5A, I_{B} = 50mA$
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}	_	0.89	1.0	V	$I_{C} = 2.5A, I_{B} = 50mA$
Base-Emitter Turn-on Voltage (Note 8)	V _{BE(on)}	_	079	_	V	$I_{C} = 2.5A, V_{CE} = 2V$
Transitional Frequency	f⊤	100	140	_	MHz	$I_{C} = 50 \text{mA}, V_{CE} = 10 \text{V}, f = 100 \text{MHz}$
Output capacitance	Cobo	_	23	30	pF	V _{CB} = 10V, f = 1MHz
Switching Time	t _{on}	_	170	_	ns	$V_{CC} = 10V, I_C = 1A,$
Switching Time	t _{off}		400		ns	$I_{B1} = -I_{B2} = 10 \text{mA}$

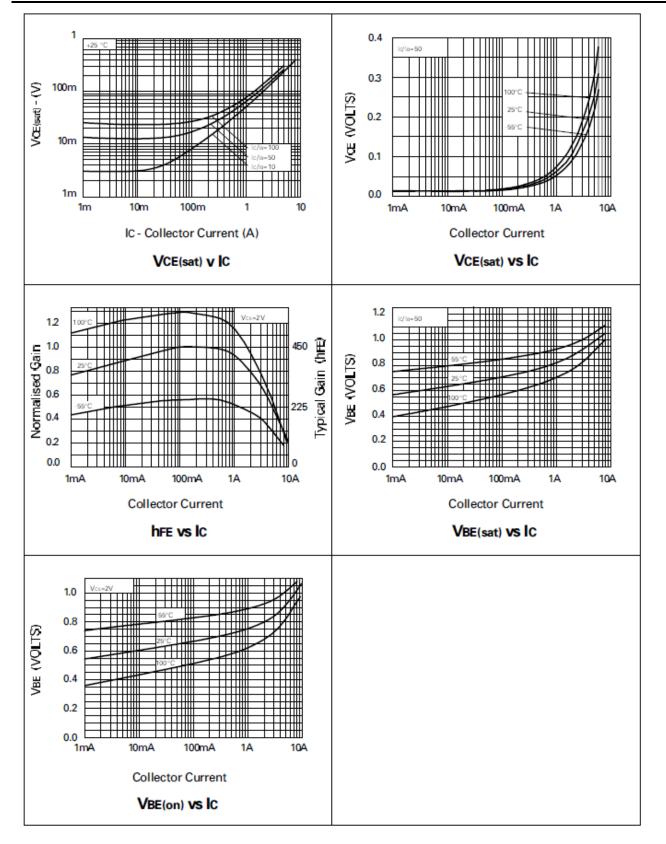
NDN Electrical Characteristics 2500 ~ ~ .+6 sified)

8. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%. Note:





NPN – Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV CBO	-20	-65	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-20	-55	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	-8.8	—	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	_	_	-0.1	μA	V _{CB} = -15V
Emitter Cutoff Current	I _{EBO}	—		-0.1	μA	$V_{EB} = -4V$
		300	475	_	- - - -	$I_{C} = -10mA, V_{CE} = -2V$ $I_{C} = -100mA, V_{CE} = -2V$ $I_{C} = -2A, V_{CE} = -2V$
		300	450	—		
DC aurrent transfer Static ratio (Nata 0)	hfe	150	230	—		
DC current transfer Static ratio (Note 8)		35	70	—		$I_{\rm C} = -4A, V_{\rm CE} = -2V$
		_	30	—		$I_{\rm C} = -6A, V_{\rm CE} = -2V$
		_	-16	-40		I _C = -100mA, I _B = -10mA
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	_	-130	-200	mV	$I_{C} = -1A, I_{B} = -20mA$
			-190	-260		I _C = -2.5A, I _B = -200mA
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}	—	-0.98	-1.1	V	I _C = -2.5A, I _B = -200mA
Base-Emitter Turn-on Voltage (Note 8)	V _{BE(on)}	_	-0.85		V	$I_{C} = -2.5A, V_{CE} = -2V$
Transitional Frequency	fT	150	180	_	MHz	$I_{C} = -50 \text{mA}, V_{CE} = -10 \text{V}, f = 100 \text{MHz}$
Output capacitance	C _{obo}	—	21	30	pF	V _{CB} = -10V, f = 1MHz,
Switching Time	t _{on}		40		ns	$V_{CC} = -10V, I_C = -1A,$
Switching Time	t _{off}		670] —	ns	$I_{B1} = -I_{B2} = -20 \text{mA}$

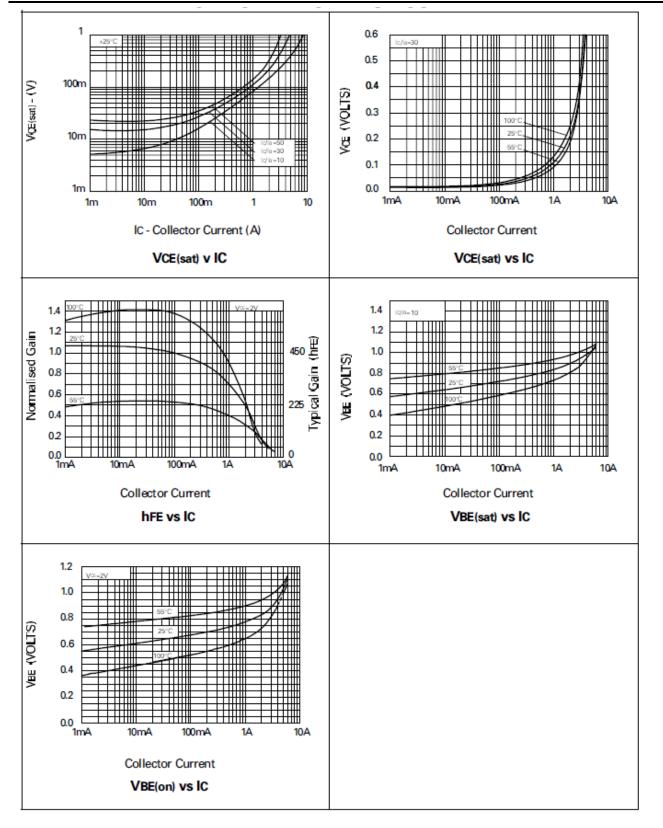
PNP - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Note: 8. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.





PNP – Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

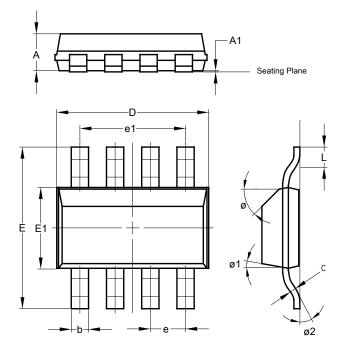






Package Outline Dimensions

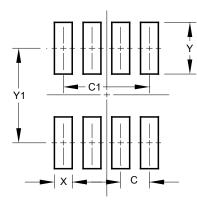
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SM-8						
Dim	Min Max Typ						
Α		1.70	1.60				
A1	0.02	0.10	0.04				
b	0.70	0.90	0.80				
С	0.24	0.24 0.32 0.28					
D	6.30	6.30 6.70 6.60					
е	1.53 REF						
e1		4.59 RE	F				
Е	6.70	6.70 7.30 7.00					
E1	3.30	3.70	3.50				
L	0.75 1.00 0.90						
Ø	45°						
Ø1		15°					
Ø2			10°				
All I	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.52
C1	4.6
Х	0.95
Y	2.80
Y1	6.80

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.





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